

## 60V, 55A, 8.9mΩ N-channel Power Trench MOSFET

### JMTG100N06A

#### Features

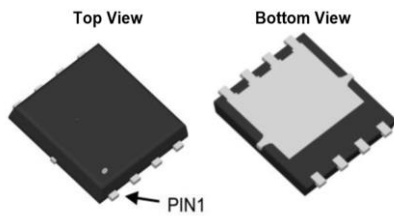
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS TESTED
- 100%  $\Delta V_{ds}$  TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

#### Applications

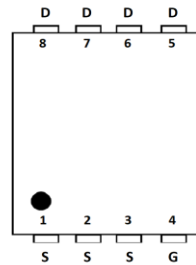
- Load Switch
- PWM Application
- Power Management

#### Product Summary

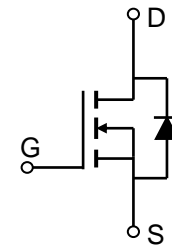
Parameters	Value	Unit
$V_{DSS}$	60	V
$V_{GS(th)_{Typ}}$	1.5	V
$I_D(@V_{GS}=10V)$	55	A
$R_{DS(ON)_{Typ}}(@V_{GS}=10V)$	7.7	mΩ
$R_{DS(ON)_{Typ}}(@V_{GS}=4.5V)$	8.9	mΩ



PDFN5x6-8L



Pin Assignment



Schematic Diagram

#### Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTG100N06A	60N04	1	Tape&Reel	PDFN5x6-8L	2500	25000

#### Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	60	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	55
		$T_C = 100^\circ\text{C}$	39
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	118	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	134
		$T_C = 100^\circ\text{C}$	54
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

#### Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	42	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	

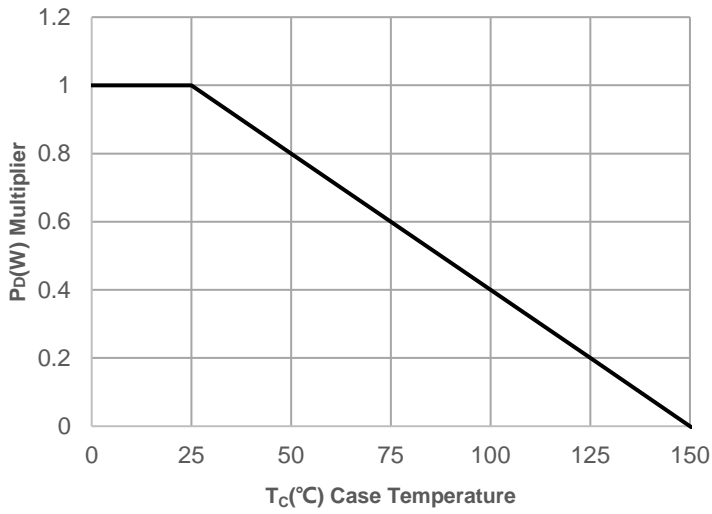
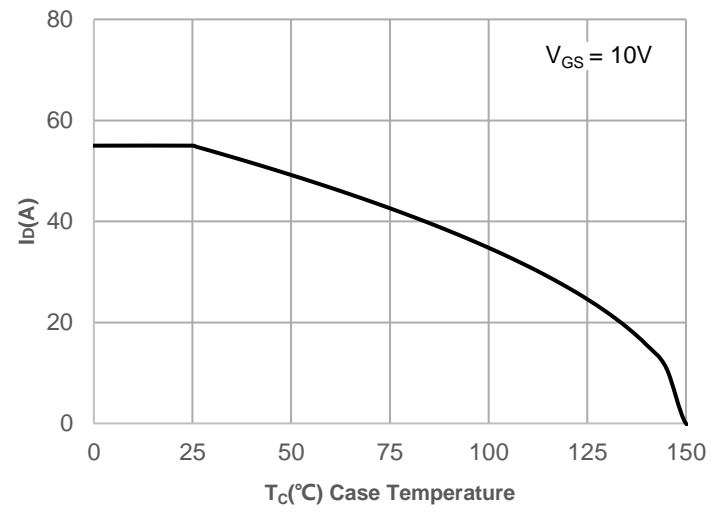
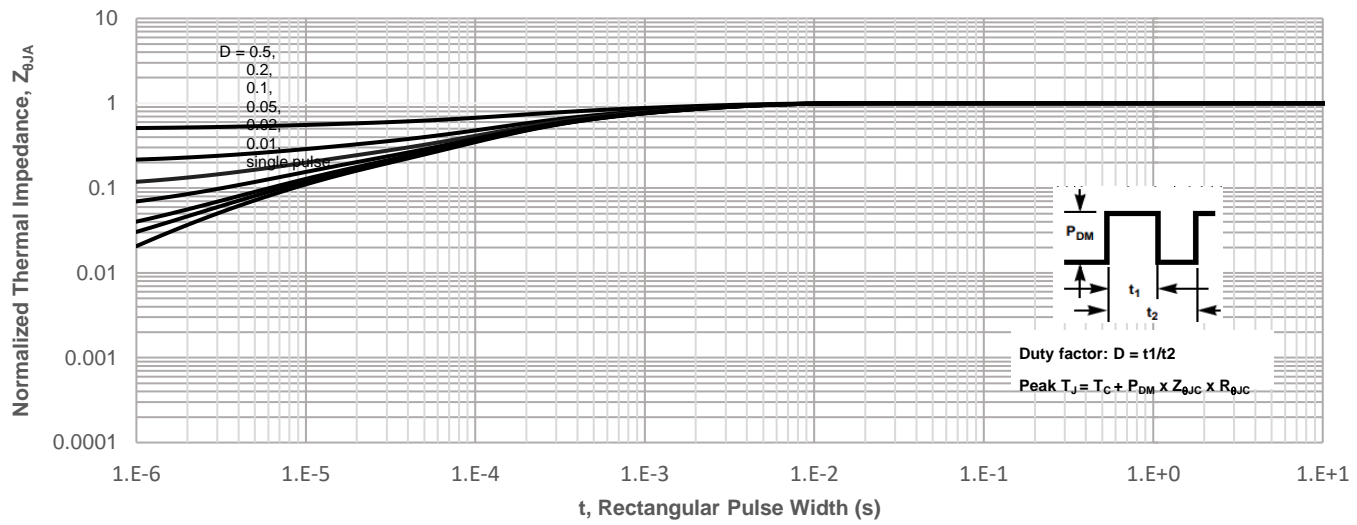
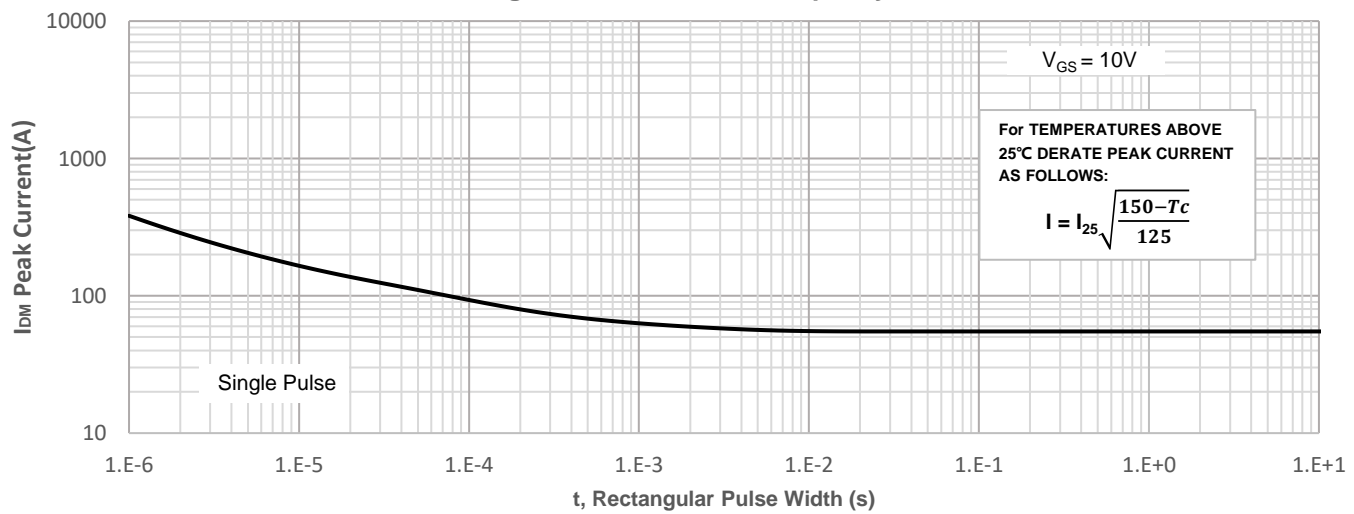
**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	1.5	2.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	7.7	10.0	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 15\text{A}$	-	8.9	11.5	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	2.2	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 30\text{V}, f = 1\text{MHz}$	-	4160	-	pF
$C_{oss}$	Output Capacitance		-	184	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	148	-	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 30\text{V}, I_D = 20\text{A}$	-	77	-	nC
$Q_{gs}$	Gate Source Charge		-	14	-	nC
$Q_{gd}$	Gate Drain("Miller") Charge		-	13	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 30\text{V}$ $I_D = 20\text{A}, R_{GEN} = 3\Omega$	-	11	-	ns
$t_r$	Turn-On Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	66	-	ns
$t_f$	Turn-Off Fall Time		-	15	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	55	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	220	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	-		1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	-	26	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	35	-	nC

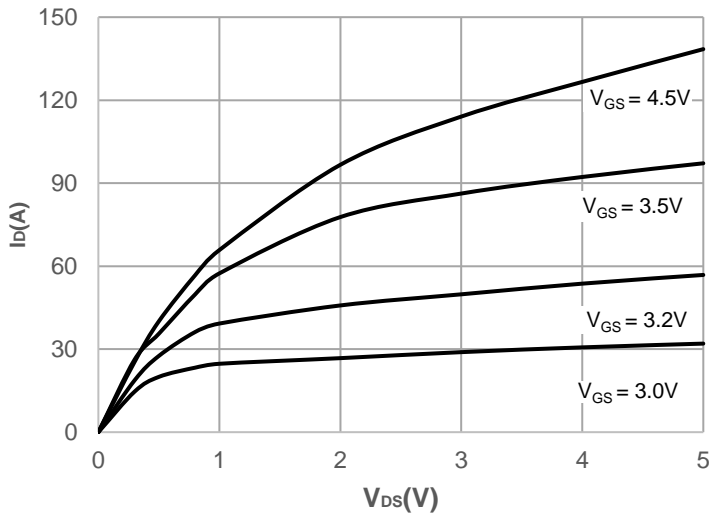
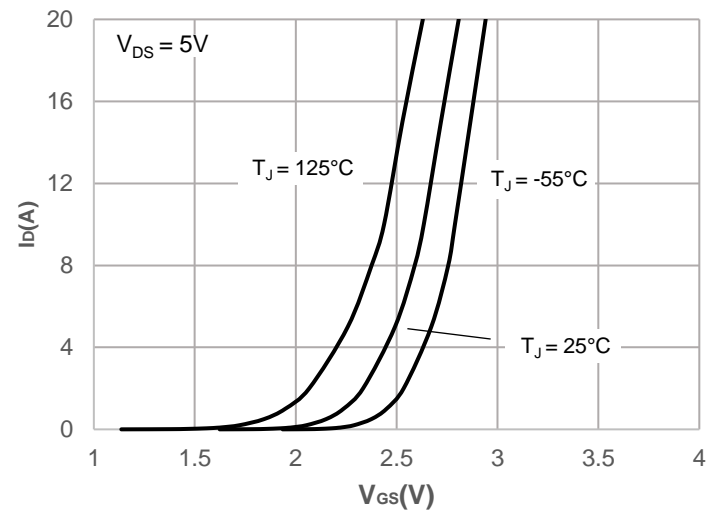
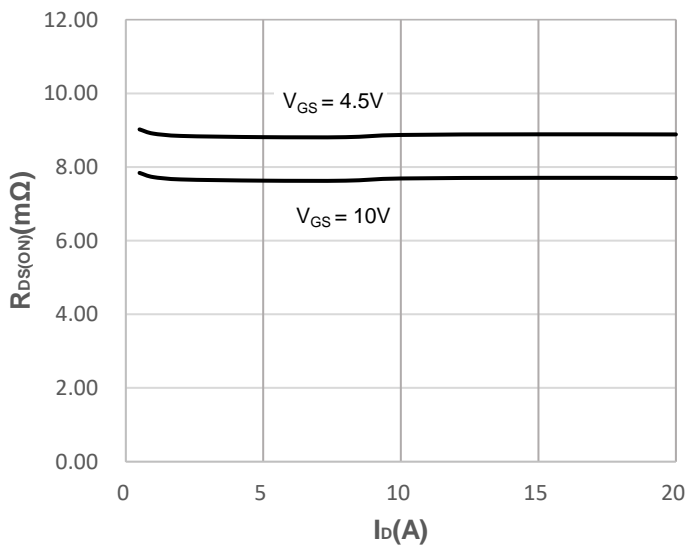
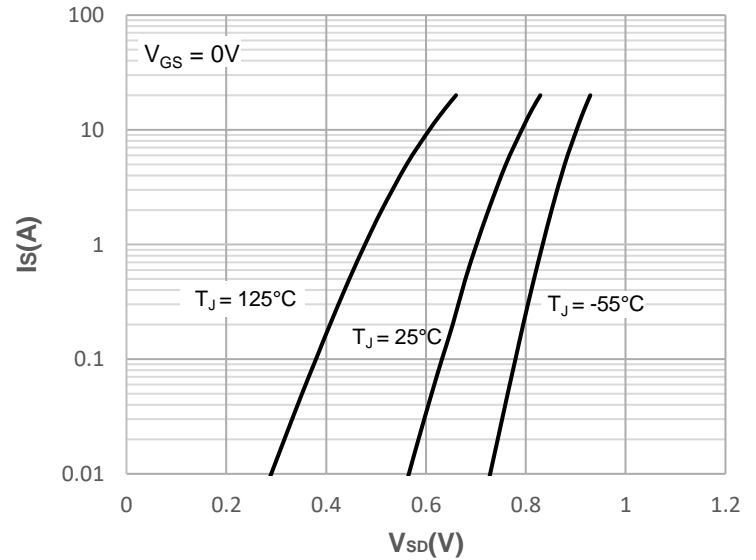
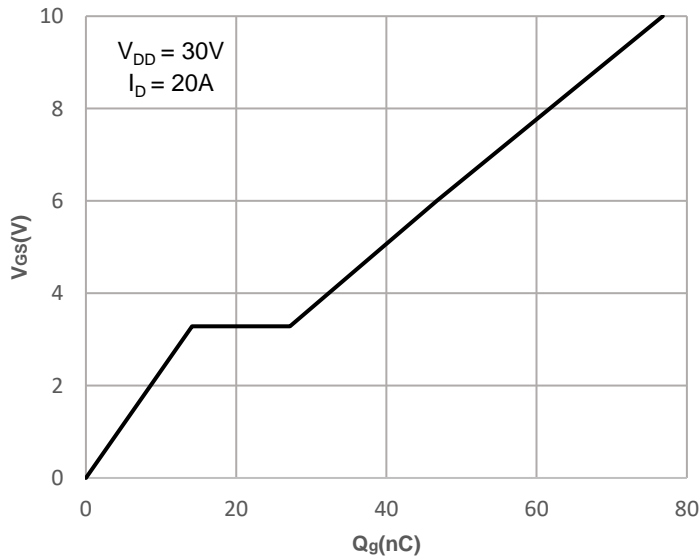
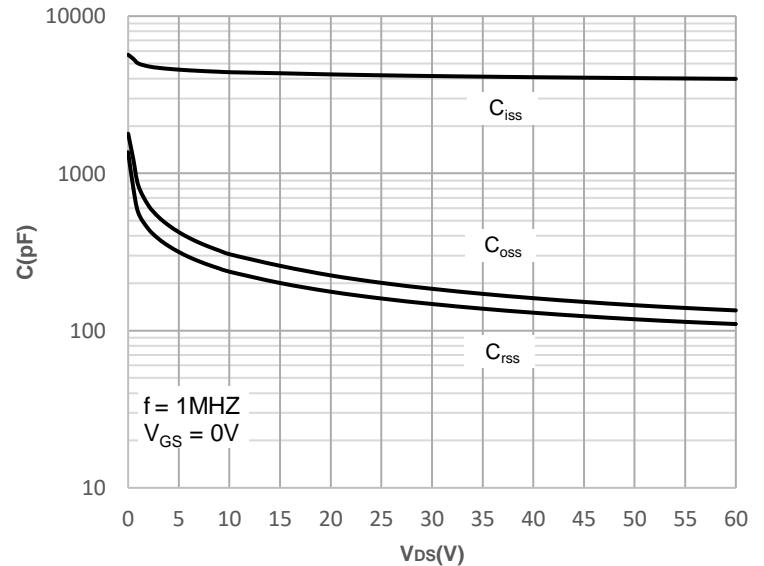
- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 30\text{V}$ ,  $V_G = 10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 0.5\text{mH}$ ,  $I_{AS} = 21.7\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a  $1\text{inch}^2$  pad of 2oz copper FR4 PCB.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .



## Typical Performance Characteristics

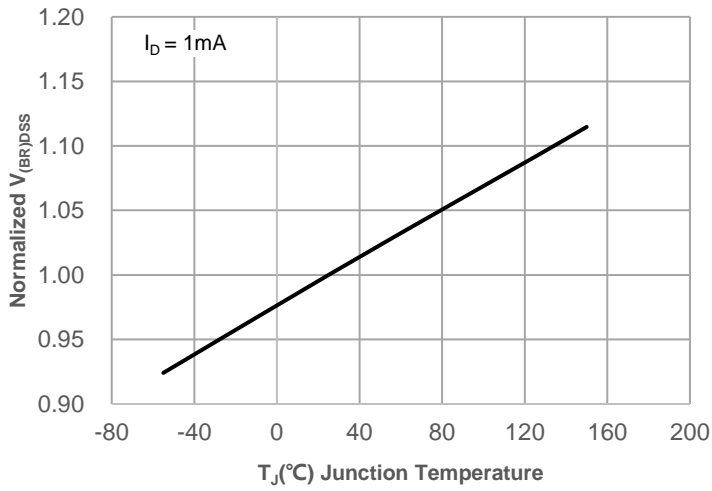
**Figure 1: Power De-rating**

**Figure 2: Current De-rating**

**Figure 3: Normalized Maximum Transient Thermal Impedance**

**Figure 4: Peak Current Capacity**


## Typical Performance Characteristics

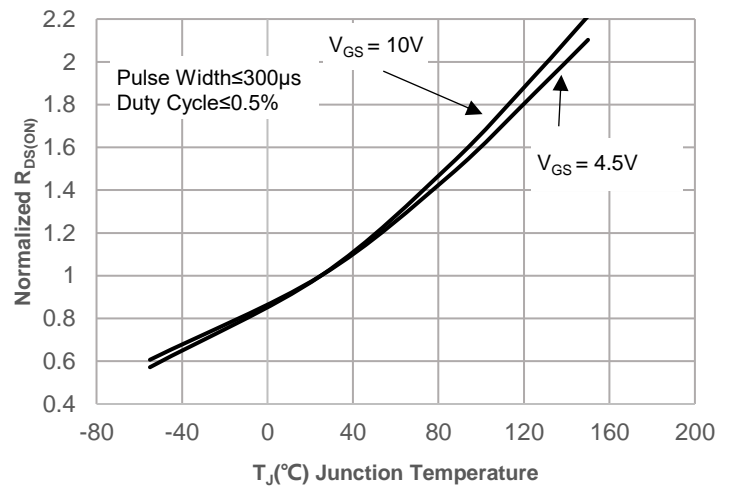
**Figure 5: Output Characteristics**

**Figure 6: Typical Transfer Characteristics**

**Figure 7: On-resistance vs. Drain Current**

**Figure 8: Body Diode Characteristics**

**Figure 9: Gate Charge Characteristics**

**Figure 10: Capacitance Characteristics**


## Typical Performance Characteristics

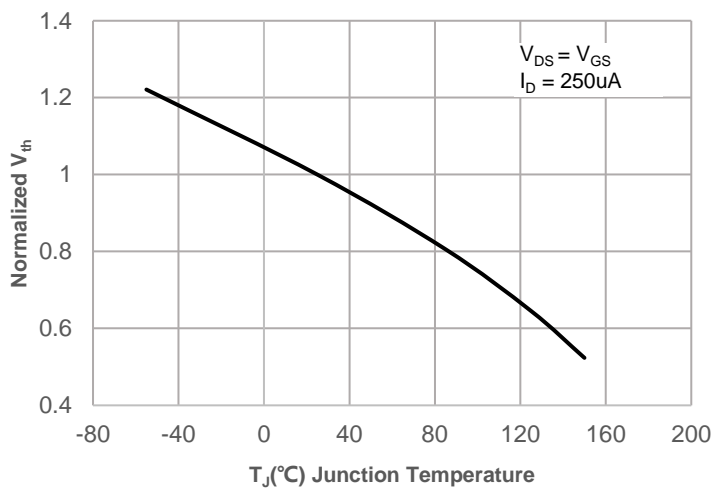
**Figure 11: Normalized Breakdown voltage vs. Junction Temperature**



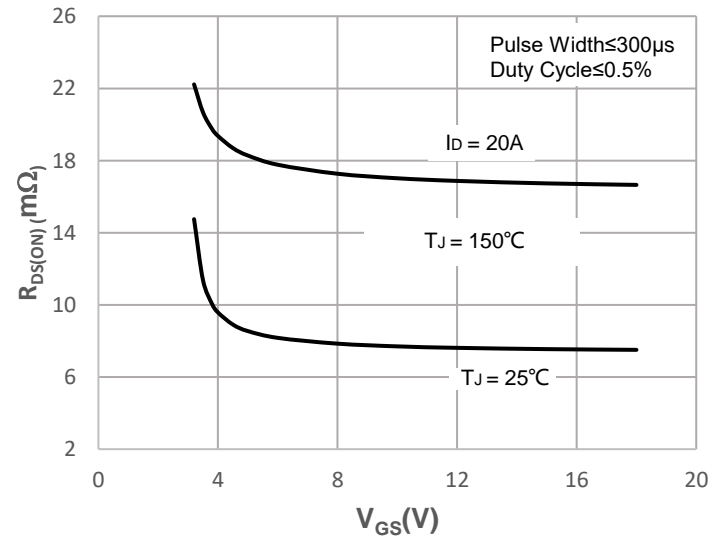
**Figure 12: Normalized on Resistance vs. Junction Temperature**



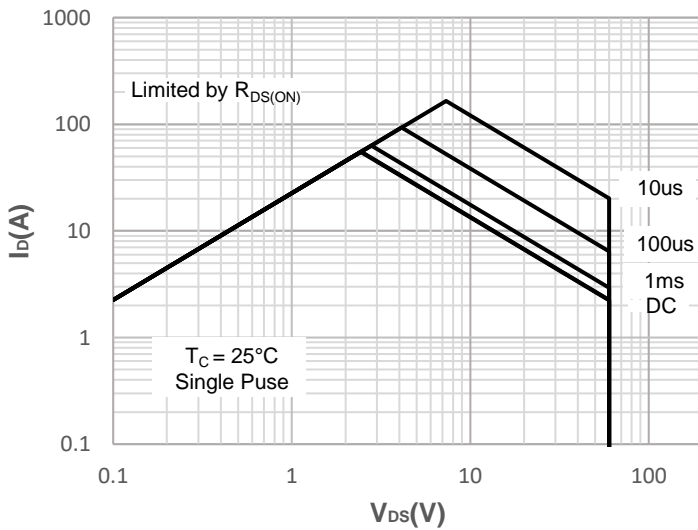
**Figure 13: Normalized Threshold Voltage vs. Junction Temperature**

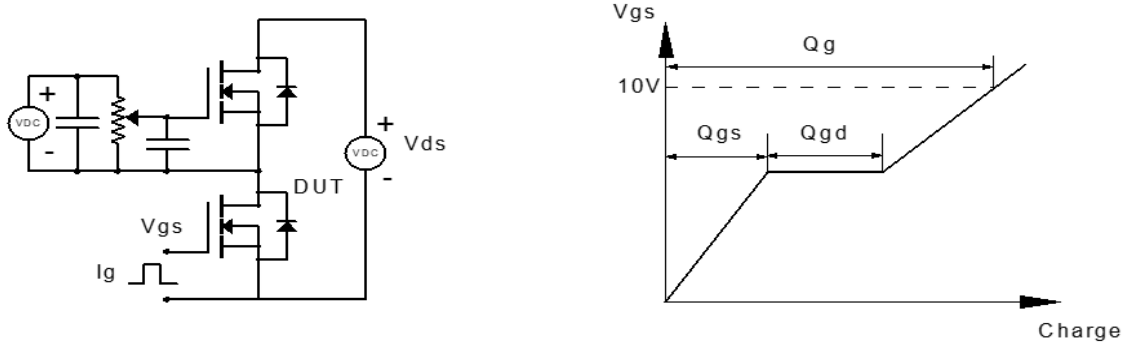
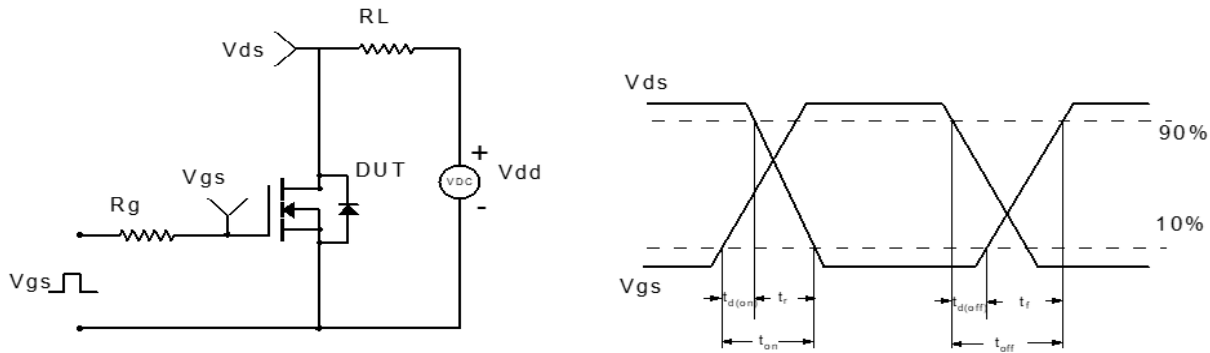
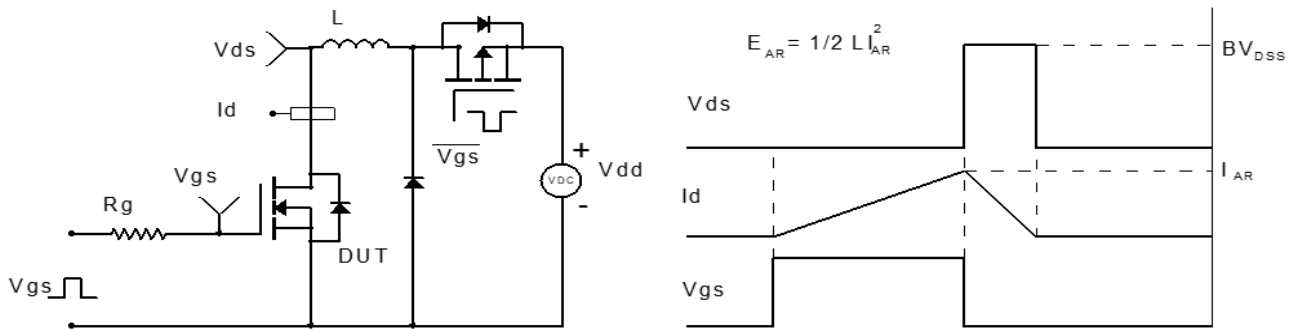
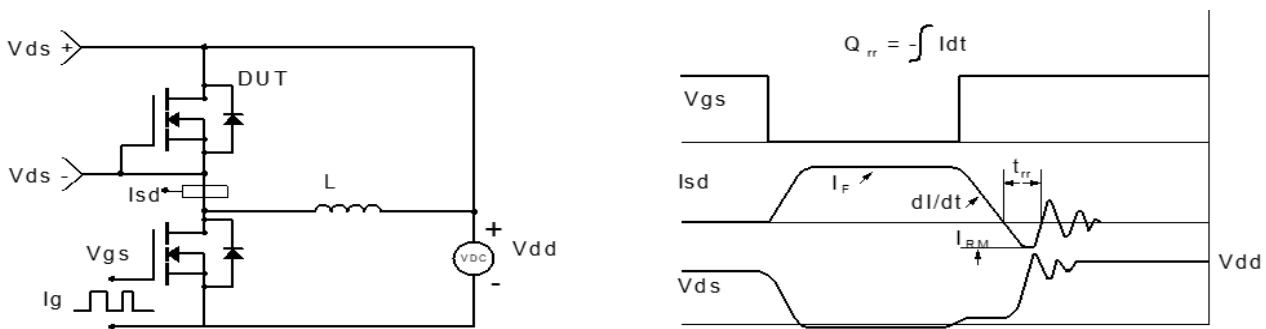


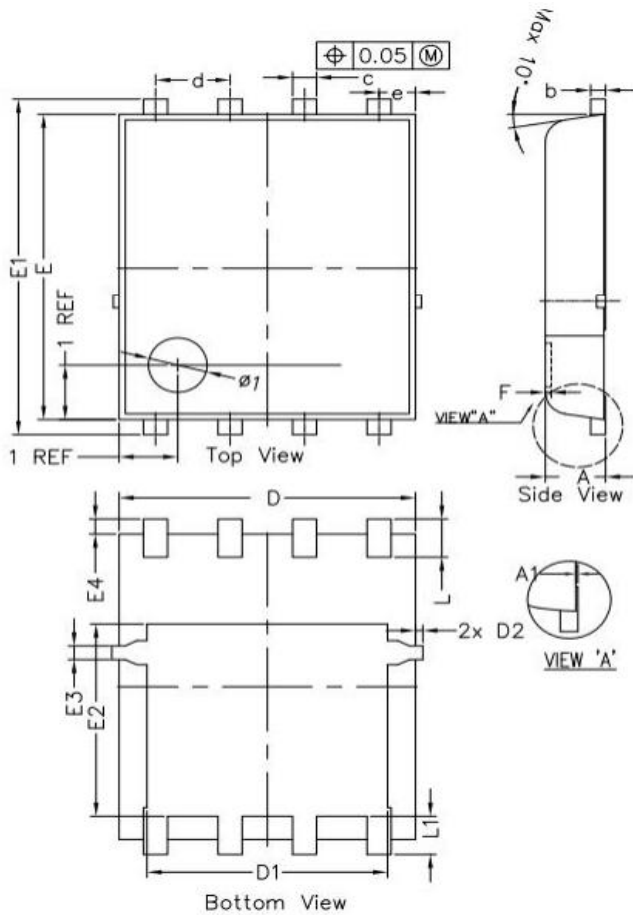
**Figure 14: R\_{DS(ON)} vs. V\_{GS}**



**Figure 15: Maximum Safe Operating Area**



**Test Circuit**

**Figure 1: Gate Charge Test Circuit & Waveform**

**Figure 2: Resistive Switching Test Circuit & Waveform**

**Figure 3: Unclamped Inductive Switching Test Circuit & Waveform**

**Figure 4: Diode Recovery Test Circuit & Waveform**


**Package Mechanical Data- PDFN5x6-8L**


SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
* A	0.900	1.000	1.100	0.035	0.039	0.043
A1	0.000	---	0.050	0.000	----	0.002
b	0.246	0.254	0.312	0.010	0.010	0.012
* c	0.310	0.410	0.510	0.012	0.016	0.020
d	1.27 BSC			0.050 BSC		
* D	4.950	5.050	5.150	0.195	0.199	0.203
D1	4.000	4.100	4.200	0.157	0.161	0.165
* D2	---	---	0.125	---	---	0.005
e	0.62 BSC			0.024 BSC		
* E	5.500	5.600	5.700	0.217	0.220	0.224
* E1	6.050	6.150	6.250	0.238	0.242	0.246
E2	3.425	3.525	3.625	0.135	0.139	0.143
E3	0.150	0.250	0.350	0.006	0.010	0.014
* E4	0.175	0.275	0.375	0.007	0.011	0.015
F	-	-	0.100	-	-	0.004
* L	0.500	0.600	0.700	0.02	0.02	0.03
L1	0.600	0.700	0.800	0.02	0.03	0.03

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